

THS4120

EVM User's Guide for High-Speed Fully-Differential Amplifier

User's Guide

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Applying loads outside of the specified output range may result in unintended operation and/or possible permanent damage to the EVM. Please consult the EVM User's Guide prior to connecting any load to the EVM output. If there is uncertainty as to the load specification, please contact a TI field representative.

During normal operation, some circuit components may have case temperatures greater than 60°C. The EVM is designed to operate properly with certain components above 60°C as long as the input and output ranges are maintained. These components include but are not limited to linear regulators, switching transistors, pass transistors, and current sense resistors. These types of devices can be identified using the EVM schematic located in the EVM User's Guide. When placing measurement probes near these devices during operation, please be aware that these devices may be very warm to the touch.

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Preface

About This Manual

This manual is written to provide information about the evaluation module of the fully differential amplifier under test. Additionally, this document provides a good example of PCB design for high speed applications. The user should keep in mind the following points.

The design of the high-speed amplifier PCB is a sensitive process. Therefore, the user must approach the PCB design with care and awareness. It is recommended that the user initially review the data sheet of the device under test. It is also helpful to review the schematic and layout of the THS4120 EVM to determine the design techniques used in the evaluation board. In addition, it is recommended that the user review the application note *Fully-Differential Amplifiers* (literature number SLOA054B) to gain more insight about differential amplifiers. This application note reviews the differential amplifiers and presents calculations for various filters.

How to Use This Manual

- Chapter 1—Introduction and Description
- Chapter 2—Using the THS4120 EVM
- Chapter 3—General High-Speed Amplifier Design Considerations

Information About Cautions and Warnings

This book may contain cautions and warnings.

This is an example of a caution statement.

A caution statement describes a situation that could potentially damage your software or equipment.

This is an example of a warning statement.

A warning statement describes a situation that could potentially cause harm to you.

The information in a caution or a warning is provided for your protection. Please read each caution and warning carefully.

Related Documentation From Texas Instruments

- THS4120 data sheet (literature number SLOS319A)
- Application report (literature number SLOA054B),
Fully-Differential Amplifiers

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Introduction and Description

The Texas Instruments THS4120 evaluation module (EVM) helps designers evaluate the performance of the THS4120 operational amplifier. Also, this EVM is a good example of high-speed PCB design.

This document details the Texas Instruments THS4120 high-speed operational amplifier evaluation module (EVM). It includes a list of EVM features, a brief description of the module illustrated with a series of schematic diagrams, EVM specifications, details on connecting and using the EVM, and a discussion of high-speed amplifier design considerations.

This EVM enables the user to implement various circuits to clarify the available configurations presented by the schematic of the EVM. In addition, the schematic of the default circuit has been added to depict the components mounted on the EVM when it is received by the customer. This configuration correlates to the single input/differential output signal.

Other sample circuits are presented to show how the user can implement other circuit configurations such as differential input/differential output signal, transformer utilization on the input and output terminals, VICR level shifter, and Butterworth filter with multiple feedback. The user may be able to create and implement circuit configurations in addition to those presented in this document using the THS4120 EVM.

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1.1 Description

This EVM is made of the THS4120 high-speed operational amplifier, a number of passive components, and various features and component footprints that enable the user to experiment and verify various operational amplifier circuit configurations. Initially, this board is populated for a single-ended input/differential-output amplifier (see Figure 1-2 for populated circuits). The outputs (V_{O+} and V_{O-}) can be tested differentially or single ended. Gain is set to one and can be changed by changing the ratios of the feedback and gain resistors (see the device datasheet for recommended resistor values). Each input is terminated with a 50- Ω resistor to provide correct line-impedance matching.

This EVM is optimized to work with ± 1.65 power supplies. If the user tests the device in a single supply mode ($V_{DD} = 3.3$ V), then the proper grounding should be applied. The V_{OCM} voltage level would be set at the mid rail (1.65-V when $V_{DD} = 3.3$ V). In general, the mid rail is the optimal area of the operation for amplifiers. Therefore, if the device is operating at $V_{DD} = 3.3$ V, it is recommended that a dc offset be added to the input signal to shift it to the mid rail. Having the input signal centered at the mid rail reduces the peaking effect. RPU resistors in this EVM work as input signal level shifters. Therefore, they can be used to shift the input signal level. To calculate the RPU values use the following equation.

$V_{(p)} = V_{(pullup)}$, RPU = R pullup (see EVM schematic)

$$RPU = \frac{V_{(p)} - V_{DD}}{(V_I - V_{(p)}) \times \frac{1}{R_g} + (V_O - V_{(p)}) \times \frac{1}{R_f}}$$

The above equation is a good estimation tool for RPU. The user should consider the component error contribution to the system. As a result, the RPU number generated by the above equation could be changed slightly to compensate for the error to provide the optimal result.

Having V_{OCM} level at 1.65 V above the GND causes a current flow from V_{OCM} to GND. Consideration should be given to this current flow which will increase the I_{DD} .

1.2 Evaluation Module Features

THS4120 high-speed operational amplifier EVM features include:

- Single and differential input and output capability
- Nominal 50- Ω input and output termination resistors. They can be configured according to the application requirement.
- V_{OCM} direct input control (see schematic and the device data sheet)
- V_{OCM} pin can be controlled via transformer center-tap (see schematic)
- Shutdown pin control, JU1 (if applicable to the device, see the device data sheet)
- Input and output transformer footprints for changing single-ended signals to differential signals

- Footprints for high-precision, balanced feedback and gain resistors (0.01% or better)
- Footprints for low-pass filter implementation (see application note SLOA054A)
- Footprints for antialiasing filter implementation (see application note SLOA054A)
- Differential probe terminals on input and output nodes for differential probe insertion
- Various GND and signal test points on the PCB
- Circuit schematic printed on the back of the EVM
- A good example of high-speed amplifier PCB design and layout

1.3 THS4120 EVM Specifications

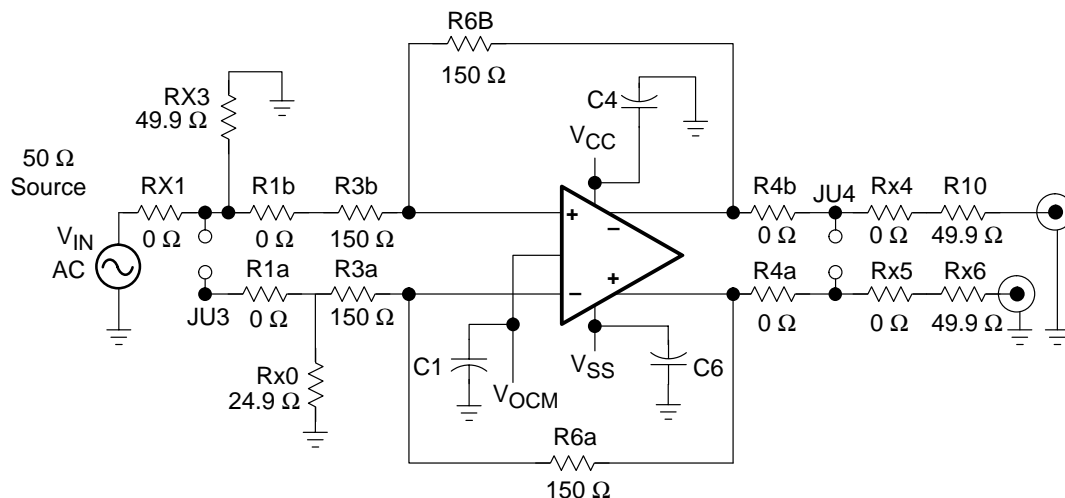
Supply voltage range (see the device data sheet)
 Supply current, I_{CC} (see the device data sheet)
 Output drive, I_O (see the device data sheet)

For complete THS4120 amplifier IC specifications, parameter measurement information, and additional application information, see the THS4120 data sheet, TI literature number SLOS319.

1.4 Schematic of the Populated Circuit (Default Configuration)

For verification of jumper locations and other bypass components, see the complete EVM schematic in Figure 1–2.

Figure 1–1. Schematic of the Populated Circuit on the EVM (Default Configuration)

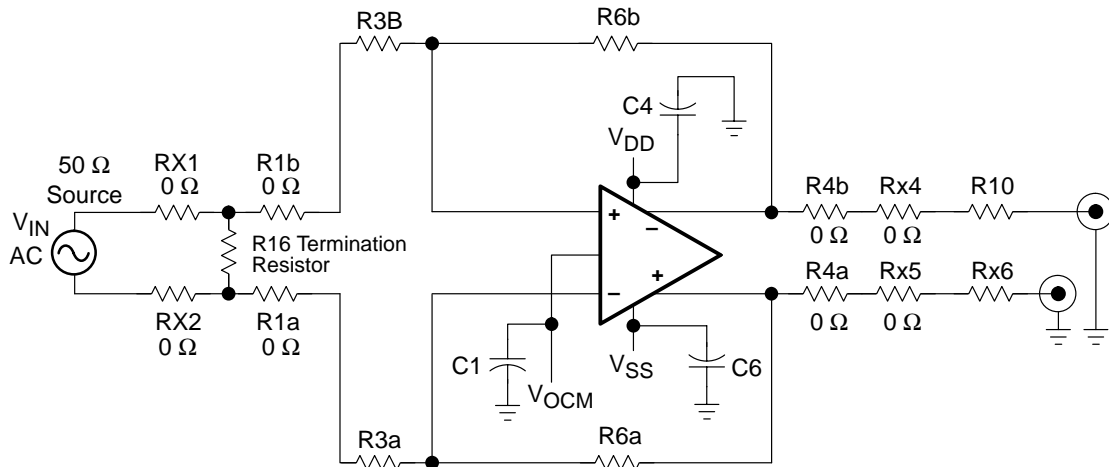


NOTE: Default populated footprints on the EVM from the input nodes to the output terminals Gain = 1

1.6 Additional Sample Schematics

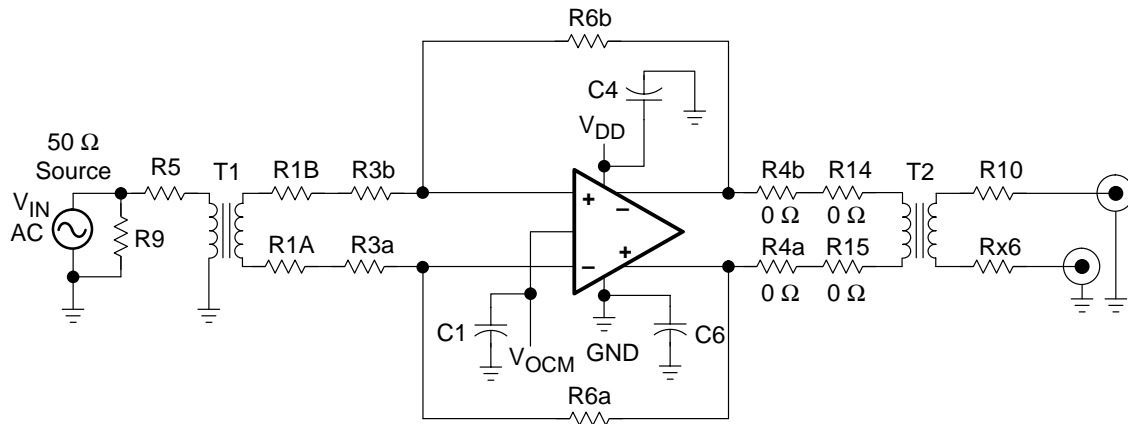
For verification of jumper locations and other bypass components, see the complete EVM schematic in Figure 1–2.

Figure 1–3. Fully-Differential In/Fully-Differential Out, Without Transformer



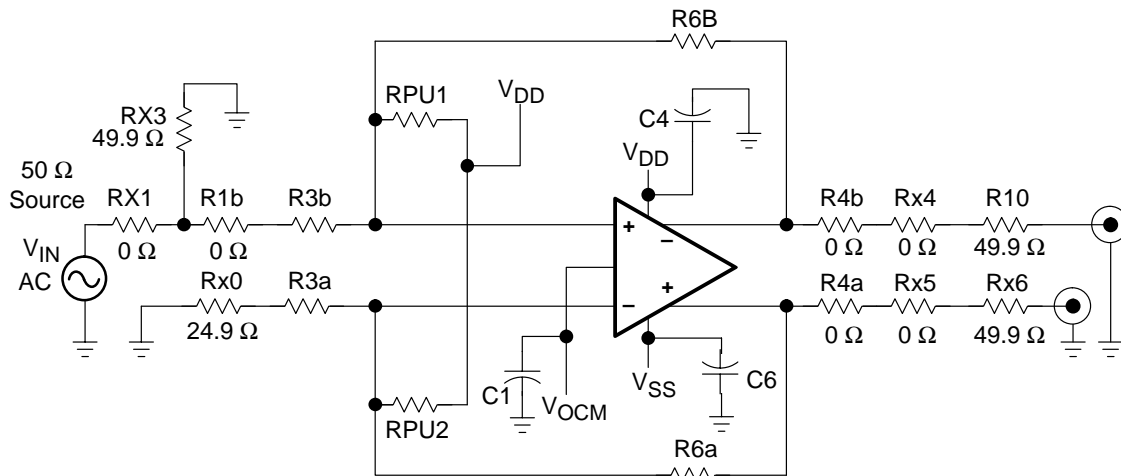
Note: Fully-differential in / fully-differential out signal path. See the *Texas Instruments February 2001 Analog Applications Journal* for the information on the termination resistors.

Figure 1–4. Fully-Differential In/Fully-Differential Out, Utilizing Transformer



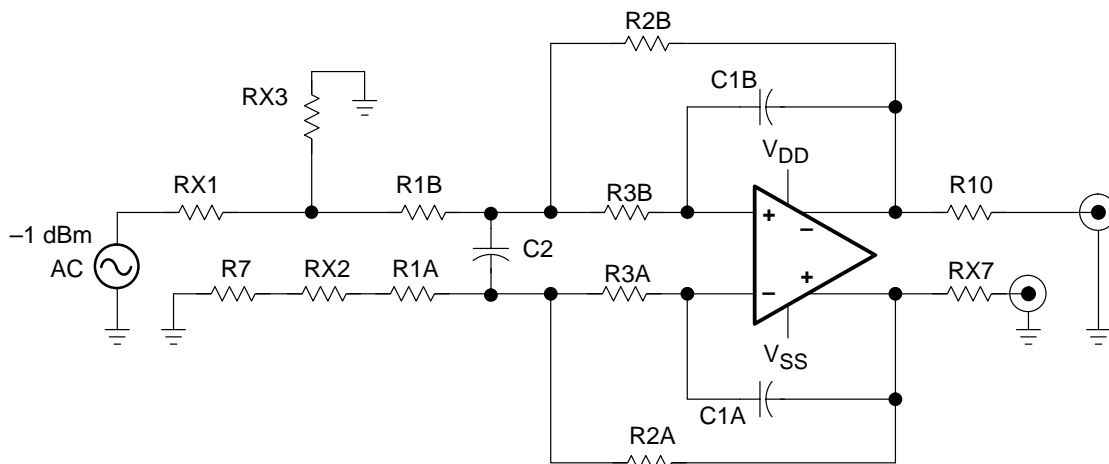
Note: Utilizing the input and output transformers to create a fully-differential signal input/ differential or single output and isolate the amplifier from the rest of the front-end and back-end circuits.

Figure 1–5. VICR Level Shifter



Note: Shifting the VICR within the specified range in the data sheet via RPU1 and RPU2 if the VICR is out of the specified range. See the Application section of the data sheet for the THS4120 for more information.

Figure 1–6. Butterworth Filter With Multiple Feedback.



Note: Butterworth filter implemented with multiple feedback architecture

1.7 THS4120 EVM Layout

Figure 1–7. Top Layer (Silkscreen)

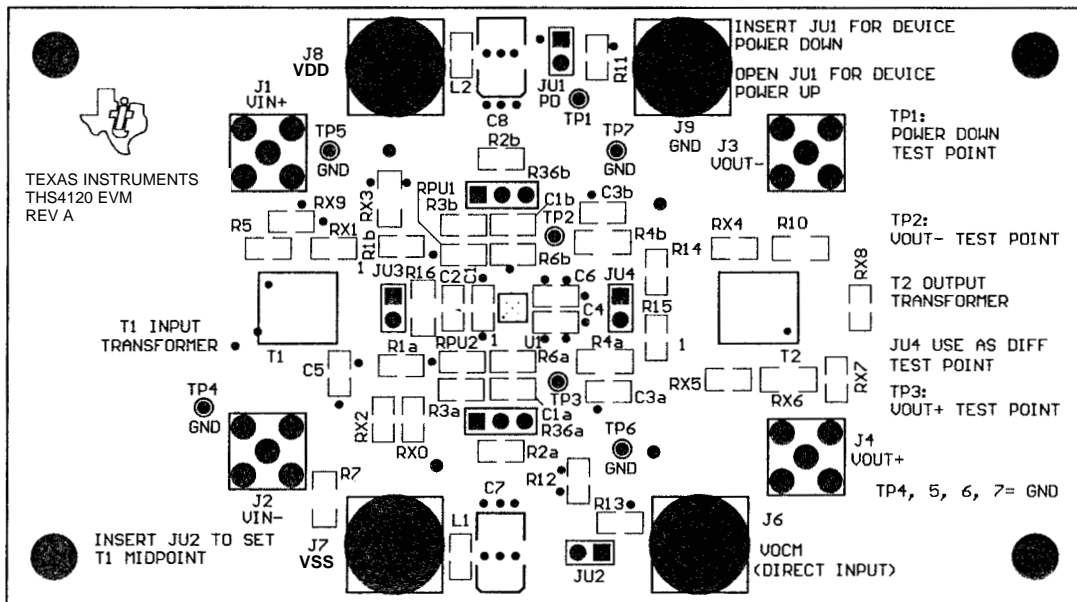


Figure 1–8. Top (Layer 1) (Signals)

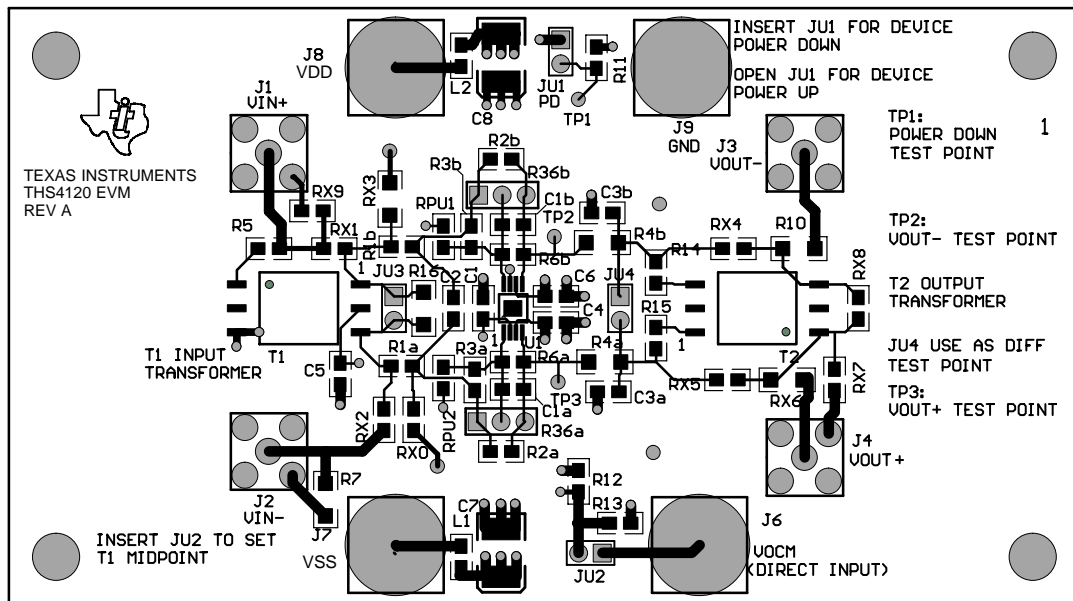


Figure 1–9. Internal Plane (Layer 2) (Ground Plane)

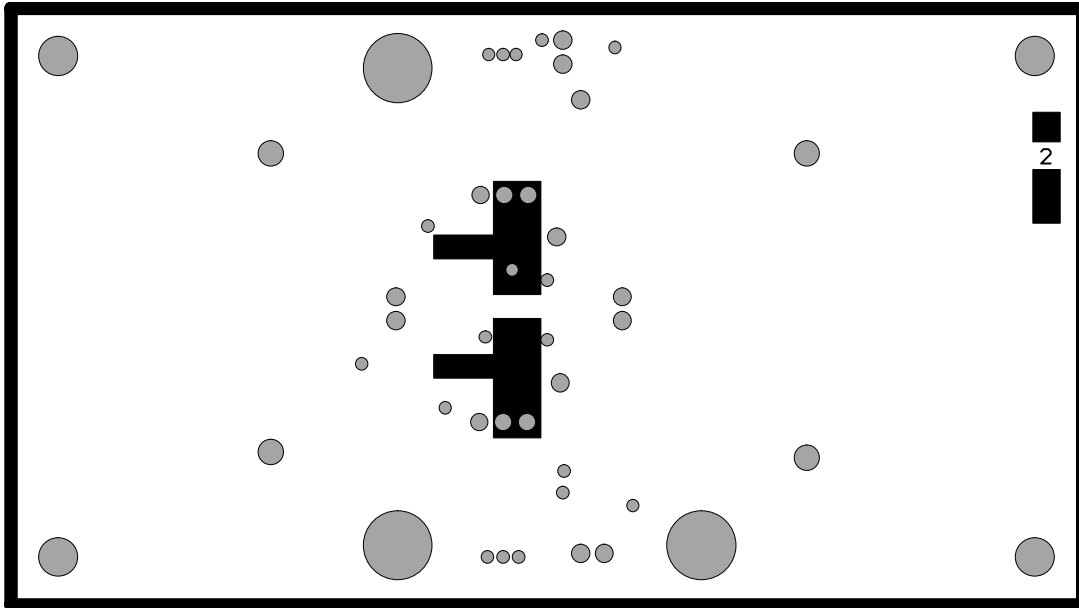


Figure 1–10. Internal Plane (Layer 3) (\pm Power Plane)

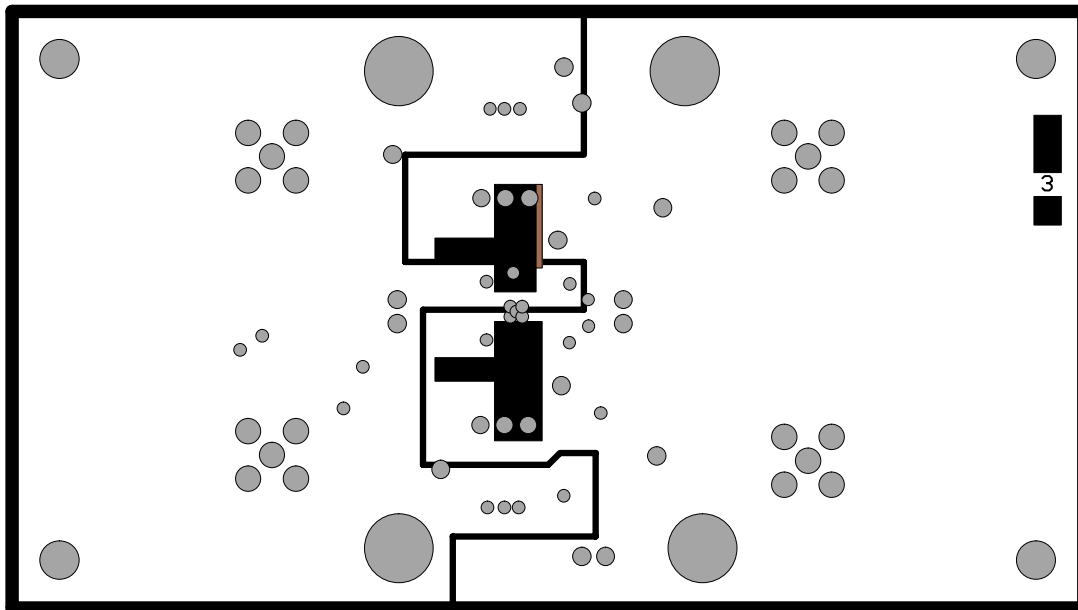
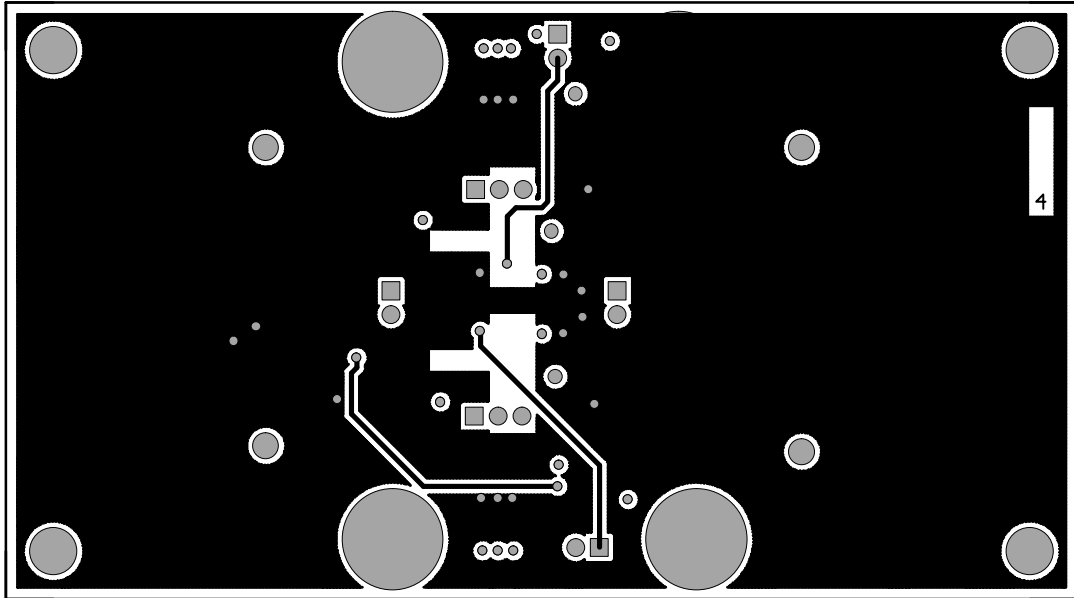


Figure 1–11. Bottom (Layer 4) (Ground and Signal)





Using the THS4120 EVM

It is recommended that the user perform the following exercises to learn the usage of the EVM. This practice helps the user learn about the various EVM terminals and their functions. In addition, it suggests the components and equipment needed to operate the EVM.

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2.1 Required Equipment

- ❑ One double-output dc power supply (± 5 V, 100 mA output minimum)
- ❑ Two dc current meters with resolution to 1 mA and capable of the maximum current the dc power supply can supply. If available, set the current limit on the dc power supply to 100 mA.

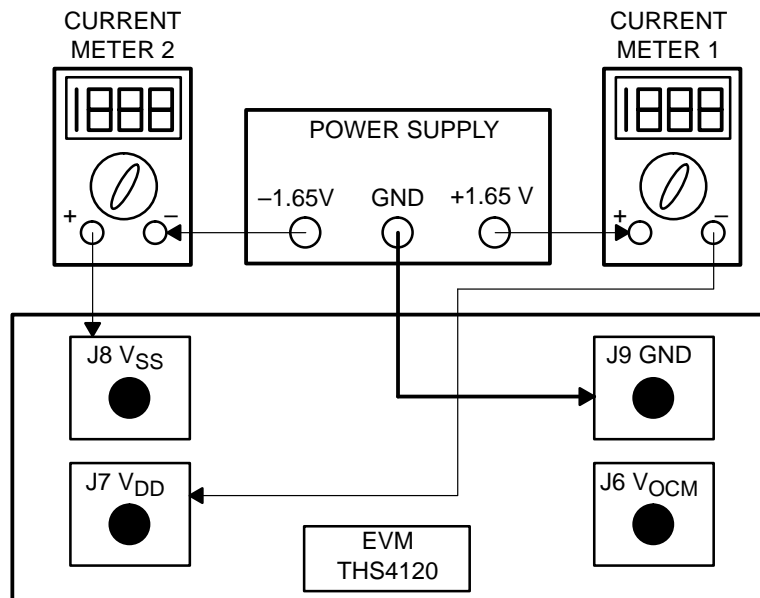
Note: Some power supplies incorporate current meters which may be applicable to this test.

- ❑ 50- Ω source impedance function generator (1 MHz, 10 V_{PP} sine wave)
- ❑ Oscilloscope (50-MHz bandwidth minimum, 50- Ω input impedance).

2.2 Power Supply Setup

- 1) Set the dc power supply to ± 1.65 V.
- 2) Make sure the dc power supply is turned off before proceeding to the next step.
- 3) Connect the positive (+) terminal of the power supply to the positive (+) terminal of the current meter number 1.
- 4) Connect the negative (-) terminal of the current meter number 1 to the V_{DD} of the EVM (J7).
- 5) Connect the common ground terminal of the power supply to the ground GND on the EVM (J9).
- 6) Connect the negative (-) terminal of the power supply to the negative (-) terminal of the second current meter.
- 7) Connect the positive (+) terminal of the current meter number 2 to the V_{SS} of the EVM (J8).

Figure 2–1. Power Supply Connection



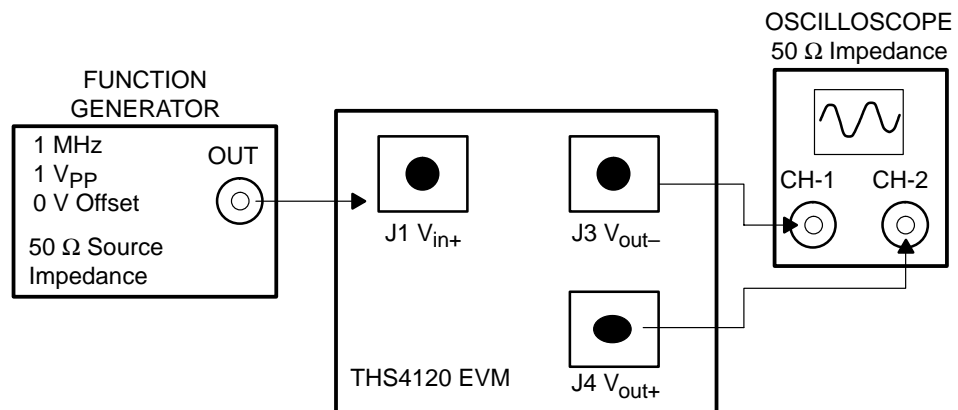
Figures are not drawn to scale.

2.3 Input and Output Setup

- 1) Ensure that JU3, JU4, and JU1 are *not installed* (open circuit).
- 2) Set the function generator to generate a 1 MHz, ± 0.5 V (1 V_{PP}) sine wave with no dc offset.
- 3) Turn off the output of the function generator before proceeding to the next step.
- 4) Using a BNC-to-SMA cable, connect the function generator to J1 (V_{in+}) on the EVM.
- 5) Using a BNC-to-SMA cable, connect the oscilloscope to J3 (V_{O-}) on the EVM.
- 6) Using a BNC-to-SMA cable, connect the oscilloscope to J4 (V_{O+}) on the EVM. Set the oscilloscope to 0.5 V/division and a time-base of 0.2 μ s/division.

Note: The oscilloscope must be set to use a 50- Ω input impedance for proper results.

Figure 2–2. Signal Connections



Figures are not drawn to scale.

2.4 Testing the EVM Setup

- 1) Turn on the dc power supply.
- 2) Verify that both the +1.65 V (current meter 1) and the -1.65 V (current meter 2) currents are below 20 mA.

Caution:

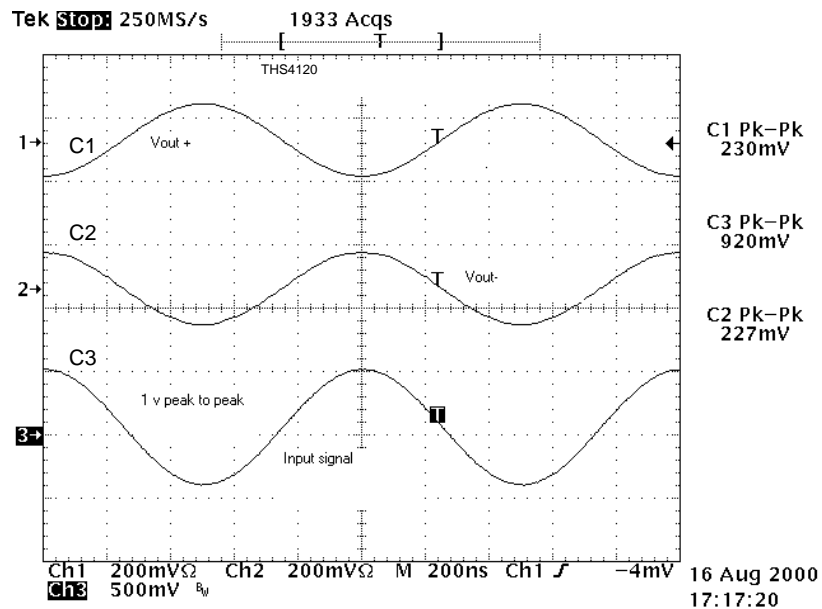
Currents above 20 mA indicate a possible short or a wrong resistor value on the PCB. Do not proceed until this situation is corrected.

- 3) Turn on the function generator.
- 4) Verify the oscilloscope is showing two 1 MHz sine waves with amplitude of ± 0.125 V. The dc offset of the signal must be below 50 mV.

Note: V_{OUT+} and V_{OUT-} should be 180 degrees out of phase. The internal attenuation of the scope should be set to 6 dB for a gain of one. Otherwise, the output will show a *gain of one-half* due to the voltage division occurring at the 50- Ω termination resistor.

Use Figure 3 as a reference for the input and output signals.

Figure 2–3. Driver 1 Output Signal



2.5 Power Down Verification

This EVM is used to evaluate devices with or without the shutdown function. Therefore, this step is only applicable if the device has a shutdown function. Please see the data sheet for power-down verification.

- 1) Insert the jumper JU1 to power down the device. The current consumption (dc current meters) should drop to less than 1 mA. Remember to discount the current flow through the 10-k Ω pullup resistor on the EVM when calculating the device current consumption in the shutdown mode.
- 2) Turn off the power supply and disconnect the wiring.
- 3) Turn off the function generator and disconnect the wiring.
- 4) Basic operation of the operational amplifier and its EVM is complete.

2.6 Measuring the Frequency Response

This EVM is designed to easily interface with network analyzers. Jumpers J3 and J4 facilitate the use and insertion of the differential probes at the input and output nodes. It is important to consider the following steps to ensure optimal performance in terms of bandwidth, phase margin, gain, and peaking

- 1) Connect the power supply according to the power supply set up (section 2.2)
- 2) Use proper load values. Loads directly effect the performance of the differential operational amplifier (the suggested value is 800 Ω differentially, 400 Ω on each output node).

Caution:

Incorrect connections cause excessive current flow and may damage the device.

- 3) Place the GND connection of the probe as close as possible to the output nodes. Use the GND holes on the EVM. The GND holes create a shorter route to the GND plane and output nodes.
- 4) Place the probe at the input nodes, set the power level of the network analyzer to the proper level (information in the data sheet typically is produced at -20 dBm power level), and calibrate the network analyzer.

Note:

If a differential probe is used, verify that resistors R1a, R1b, R4b, and R4a are in place. The 0- Ω resistors provide the path to the differential probe terminals.

- 5) Place the probe at the output nodes (if a differential probe is used, insert the probe into the provided jumper), and measure the frequency response.

Note:

Transformers are used to change the single ended signals to differential signal or vice versa. On this EVM, they can be populated according to the application or the experiment. The V_{OCM} pin of the device may be connected to the center-tap of the transformer, or maybe set via an external source such as V_{ref} of a data converter. If the V_{OCM} pin is not connected to an external source, it will be set at the center point of the power supply. For example, if ± 1.65 sources are used, the V_{OCM} level will be set to zero.

2.7 Butterworth Filter

An example of a Butterworth filter implemented with multiple feedback architecture is provided. The following circuit is implemented on the EVM board. The following figures represent the circuit configuration and the component values. The corner frequency of the filter (-3dB) is set at 1 MHz.

For verification of jumper locations and other bypass components, see the complete EVM schematic in Figure 1–2.

Figure 2–4. Multiple Feedback Filter Circuit

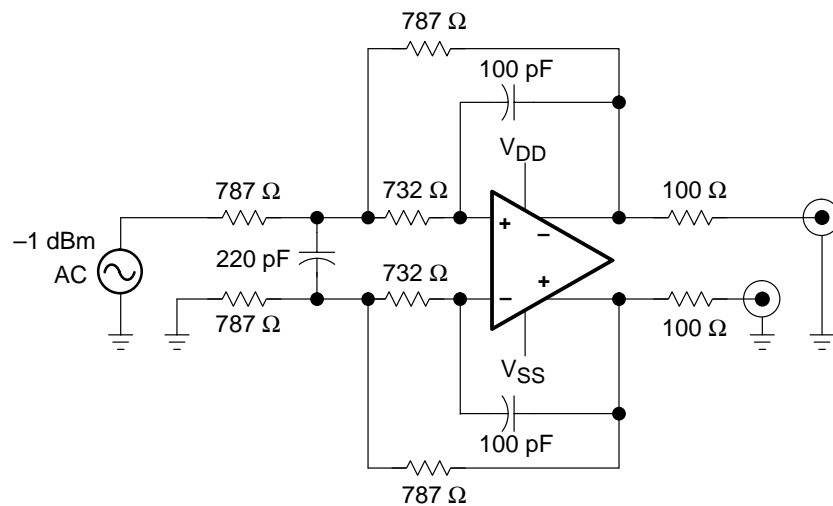
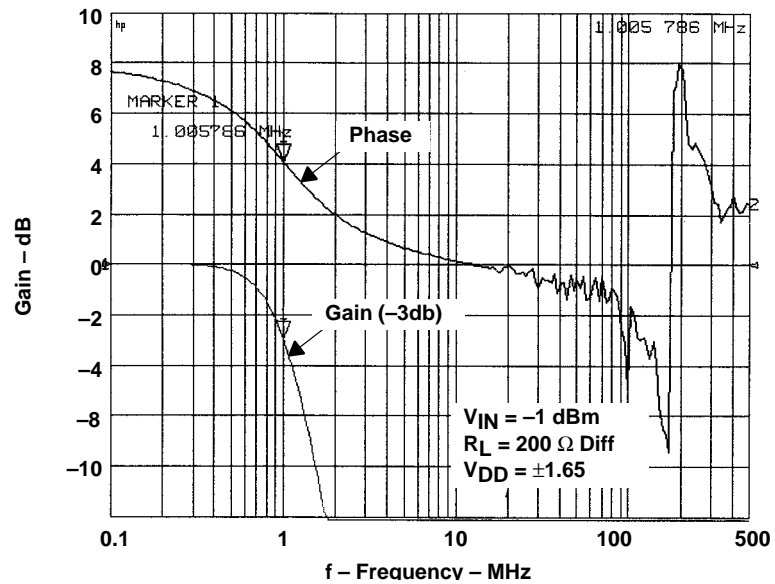


Figure 2–5. Gain vs Phase

Butterworth filter with multiple feedback frequency response.



2.8 THS4120 EVM Bill of Materials

Table 2–1. THS4120 EVM Bill of Materials

| Ref. | Description | Size | Qty. | Manufacturer | Part Number |
|--|---|------------|------|--------------|-----------------|
| C1, C4, C5, C6 | Capacitor, 0.1 μ F, ceramic | 0805 | 4 | Murata | GRM40-X7R104K25 |
| C7, C8 | Capacitor, 6.8 μ F, 35 V, 20% tantalum, SM | 7343 | 2 | Sprague | 293D685X9035D2T |
| C1A, C1B, C2, C3A, C3B | Open | 0805 | 5 | | |
| J1, J2, J3, J4 | SMT_PCB_MT | SMA jack | 4 | Amphenol | 901-144-8RFX |
| J6, J7, J8, J9 | Banana jack | | 4 | Newark | 35F865 |
| JU1, JU2, JU3, JU4 | 2 post jumper header, 0.1 centers, 0.025" square pins | 2 pos jump | 4 | | |
| JU1, JU2 | Shorting jumpers header, 0.1 centers, 0.025" square pins | | 2 | | |
| L1, L2 | Inductor, 0.22 μ H SM | 0805 | 2 | Digi-Key | PCD1176CT-ND |
| R1a, R1b, RX1, RX4, RX5 | Resistor, 0 Ω , 1% | 0805 | 5 | Digi-Key | P0.0ACT-ND |
| R2a, R2b, R5, R12, R13, R14, R15, RX2, RX7, RX8, RX9 | Open | 0805 | 11 | | |

Table 2–1. THS4120 EVM Bill of Materials (continued)

| Ref. | Description | Size | Qty. | Manufacturer | Part Number |
|-------------------------------------|------------------------------|--------------|------|-------------------|-------------|
| R3a, R3b | Resistor, 150 Ω , 1% | 0805 | 2 | Digi-Key | |
| R4a, R4b | Resistor, 0 Ω , 1% | 1206 | 2 | Digi-Key | P0.0ECT-ND |
| R6a, R6b | Resistor, 150 Ω , 1% | 0805 | 2 | Digi-Key | |
| R11 | Resistor, 10 k Ω , 1% | 0805 | 1 | Digi-Key | P10.KCTR-ND |
| R10, RX3, RX6 | Resistor, 49.9 Ω , 1% | 1206 | 3 | Digi-Key | P49.9FTR-ND |
| R16, R7 | Open | 1206 | 2 | | |
| R36aA, R36aB, R36bA, R36bB | High precision resistor | | 2 | | |
| RPU1, RPU2 | Open | 0805 | 2 | | |
| RX0 | Resistor, 24.9 Ω , 1% | 0805 | 1 | Digi-Key | P24.9CTR-ND |
| T1, T2 | Open | MC KK81 | 2 | | |
| TP1, TP2, TP3 | Test point 2 | TP .025 | 3 | Farnell | 240-345 |
| TP4, TP5, TP6, TP7 | Test point 2 | TP .025 | 4 | Farnell | 240-333 |
| U1 | IC, THS4120 | 8 Pin DGN | 1 | Texas Instruments | THS4120CDGN |

General High-Speed Amplifier Design Considerations

The THS4120 EVM layout has been designed for use with high-speed signals and can be used as an example when designing PCBs incorporating the THS4120. Careful attention has been given to component selection, grounding, power supply bypassing, and signal path layout. Disregarding these basic design considerations could result in less than optimum performance of the THS4120 high-speed operational amplifier.

Surface-mount components were selected because of the extremely low lead inductance associated with this technology. This helps minimize both stray inductance and capacitance. Also, because surface-mount components are physically small, the layout can be very compact.

Tantalum power supply bypass capacitors at the power input pads help supply currents needed for rapid, large signal changes at the amplifier output. The 0.1- μ F power supply bypass capacitors were placed as close as possible to the IC power input pins in order to minimize the return path impedance. This improves high frequency bypassing and reduces harmonic distortion.

A proper ground plane on both sides of the PCB should be used with high-speed circuit design. This provides low-inductive ground connections for return current paths. In the area of the amplifier input pins, however, the ground plane should be removed to minimize stray capacitance and reduce ground plane noise coupling into these pins. This is especially important for the inverting pin while the amplifier is operating in the noninverting mode. Because the voltage at this pin swings directly with the noninverting input voltage, any stray capacitance would allow currents to flow into the ground plane. This could cause possible gain error and/or oscillation. Capacitance variations at the amplifier input pin of greater than 1 pF can significantly affect the response of the amplifier.

In general, it is best to keep signal lines as short and as straight as possible. Incorporation of microstrip or stripline techniques is also recommended when signal lines are greater than 1 inch in length. These traces must be designed with a characteristic impedance of either 50 Ω or 75 Ω , as required by the application. Such a signal line must also be properly terminated with an appropriate resistor.

Finally, proper termination of all inputs and outputs must be incorporated into the layout. Unterminated lines, such as coaxial cable, can appear to be a reactive load to the amplifier. By terminating a transmission line with its characteristic impedance, the amplifier's load then appears to be purely resistive, and reflections are absorbed at each end of the line. Another advantage of using an output termination resistor is that capacitive loads are isolated from the amplifier output. This isolation helps minimize the reduction in the amplifier's phase-margin and improves the amplifier stability resulting in reduced peaking and settling times.